JANTX4N24U

Obsolete (JAN/JANTX/JANTXV 4N22U, 4N23U, JAN/JANTXV 4N24U)

Features:

- Surface Mount (SM), Leadless Chip Carrier (LCC)
- 1 kV electrical isolation
- Base contact provided for conventional transistor biasing
- JAN, JANTX and JANTXV devices are processed to MIL-PRF-19500





Description:

Each isolator in this series consists of an infrared emitting diode and a NPN silicon phototransistor, which are mounted in a hermetically sealed Surface Mount, 6 Pin package. Devices are designed for military and/or harsh environments.

The JAN / JANTX / JANTXV 4N22U, 4N23U and 4N24U devices are processed to MIL-PRF-19500/486. This series of 4N products are JEDEC registered, DSCC qualified.

Please contact your local representative for more information.

Applications:

- Military equipment
- High-Reliability environments
- High voltage isolation between input and output
- Electrical isolation in dirty environments
- Industrial equipment
- Medical equipment

Ordering Information						
Part Number	Isolation Voltage (kV)	I _F (mA) Typ / Max	V _{CE} (Volts) Max	Processing MIL-PRF-19500		
JAN4N22U (Obsolete)		10 / 40	/ 40 40	486		
JANTX4N22U (Obsolete)						
JANTXV4N22U (Obsolete)						
JAN4N23U (Obsolete)						
JANTX4N23U (Obsolete)	1					
JANTXV4N23U (Obsolete)						
JAN4N24U (Obsolete)						
JANTX4N24U						
JANTXV4N24U (Obsolete)						





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Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

5 (A	
Storage Temperature Range	-65° C to +150° C
Operating Temperature Range	-55° C to +125° C
Input-to-Output Isolation Voltage	± 1.00 kVDC ⁽¹⁾
Lead Soldering Temperature [1/16 inch (1.6 mm) from case for 5 seconds with soldering iron]	260° C ⁽²⁾
ESD Class	1C

Input Diode

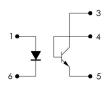
Forward DC Current (65° C or below)	40 mA
Reverse Voltage	2 V
Peak Forward Current (1 μs pulse width, 300 pps)	1 A
Power Dissipation	60 mW ⁽³⁾

Output Sensor:

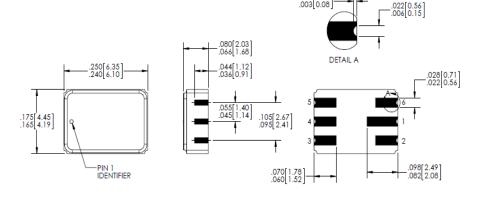
Continuous Collector Current	50 mA
Collector-Emitter Voltage	40 V
Collector-Base Voltage	45 V
Emitter-Base Voltage	4 V
Power Dissipation	300 mW ⁽⁴⁾

Notes:

- 1. Measured with input leads shorted together and output leads shorted together.
- 2. RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.
- 3. Derate linearly 1.0 mW/° C above 65° C.
- 4. Derate linearly 3.0 mW/° C above 25° C.



Pin #	LED	Pin#	Transistor
3	Collector	2	N/A
4	Base	1	Anode
5	Emitter	6	Cathode



DIMENSIONS ARE IN INCHES [MM]





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Electrical Characteristics (T_A = 25° C unless otherwise noted)

SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS	
Onput Diod	Onput Diode						
V _F	Forward Voltage	0.80 1.00 0.70	- - -	1.50 1.70 1.30	V	$I_F = 10.0 \text{ mA}$ $I_F = 10.0 \text{ mA}, T_A = -55^{\circ} C^{(1)}$ $I_F = 10.0 \text{ mA}, T_A = +100^{\circ} C^{(1)}$	
I _R	Reverse Current	-	-	100	μΑ	V _R = 2.0 V	
Output Phototransistor							
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	40	-	-	V	I _C = 1.0 mA, I _B = 0, I _F = 0	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	45	-	-	V	$I_{C} = 100 \ \mu\text{A}, I_{B} = 0, I_{F} = 0$	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	7	-	-	V	$I_E = 100 \ \mu\text{A}, \ I_C = 0, \ I_F = 0$	
I _{C(OFF)}	Collector-Emitter Dark Current	-	ı	100 100	nA μA	$V_{CE} = 20 \text{ V}, I_B = 0, I_F = 0$ $V_{CE} = 20 \text{ V}, I_B = 0, I_F = 0, T_A = 100^{\circ} \text{ C}$	
I _{CB(OFF)}	Collector-Base Dark Current	-	-	100	nA	$V_{CB} = 20 \text{ V, } I_E = 0, I_F = 0 \Omega$	
Coupled							

I _{C(ON)}	On-State Collector Current JAN / JANTX / JANTXV 4N22 [A]	0.15 2.50 1.00 1.00	- - -	- - -	mA	$\begin{split} I_F &= 2.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0 \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0 \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
	JAN / JANTX / JANTXV 4N23 [A]	0.20 6.00 2.50 2.50	- - -	- - -		$\begin{split} I_F &= 2.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0 \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0 \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
	JAN / JANTX / JANTXV 4N24 [A]	0.40 10.0 4.00 4.00	- - -	- - -		$\begin{split} I_F &= 2.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0 \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0 \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0, T_A = -55^{\circ} \text{ C}^{(1)} \\ I_F &= 10.0 \text{ mA, } V_{CE} = 5 \text{ V, } I_B = 0, T_A = 100^{\circ} \text{ C}^{(1)} \end{split}$
V _{CE(SAT)}	Collector-Emitter Saturation Voltage JAN / JANTX / JANTXV 4N22 [A] JAN / JANTX / JANTXV 4N23 [A] JAN / JANTX / JANTXV 4N24 [A]		- - -	0.30 0.30 0.30	V	I _F = 20 mA, I _C = 2.5 mA, I _B = 0 I _F = 20 mA, I _C = 5.0 mA, I _B = 0 I _F = 20 mA, I _C = 10.0 mA, I _B = 0
H _{FE}	DC Current Gain	100	-	-	V	V _{CE} = 5.0 V, I _C = 10.0 mA, I _F = 0 mA
R _{IO}	Resistance (Input-to-Output)	10 ¹¹	-	-	Ω	V ₁₀ = ± 1.0 VDC ⁽³⁾
C _{IO}	Capacitance (Input-to-Output)	-	-	5	pF	V _{I-O} = 0 V, f = 1.0 MHz ⁽³⁾
t _r , t _f	Output Rise and Fall Time	-	-	20	μs	V_{CC} = 10.0 V , I_{F} = 10.0 mA, R_{L} = 100 Ω

Notes:

- 1. Guaranteed but not tested.
- 2. Sample tested, LTPD = 10.
- 3. Measured with input leads shorted together and output leads shorted together.

General Note

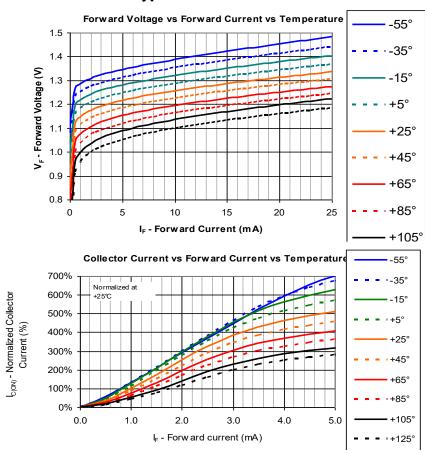
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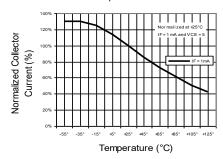


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Typical Performance Curves







Normalized Collector Current Vs Temperature

